



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

YASUMOTO, Tamihide

Serial No.: 09/995,575

Filed: November 29, 2001

Group Art Unit: 2813

Examiner: KIELIN, E.

P.T.O. Confirmation No.: 1497

For: SEMICONDUCTOR DEVICE MANUFACTURING METHOD USING METAL  
SILICIDE REACTION AFTER ION IMPLANTATION IN SILICON WIRING

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

June 12, 2003

Sir:

In response to the Office Action dated March 13, 2003, please amend the above-identified  
application as follows:

RECEIVED  
JUN 13 2003  
TECHNOLOGY CENTER 2800